TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

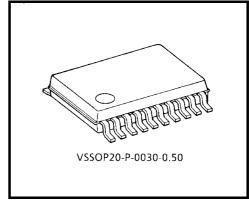
TC7MP245FK

Low-Voltage/Low-Power Octal Bus Transceiver with Bus-hold

The TC7MP245FK is a high-performance CMOS octal bus transceiver. By a low power consumption circuit, power consumption has been reduced when a bus terminal is disable state (OE=High).

The direction of data transmission is determined by the level of the DIR input. The \overline{OE} input can be used to disable the device so that the busses are effectively isolated.

But, bus of a B bus side at floating state is maintained in an appropriate logic level due to a bus hold circuit to a B bus. Moreover, the bus-hold circuit which is added to a B bus is off when \overline{OE} is low.



Weight: 0.03 g (typ.)

All inputs are equipped with protection circuits against static discharge.

Features

- Low-voltage operation : VCC = 1.65 to 3.6 V
- Low power current consumption : By a new input circuit, power consumption in \overline{OE} =H is reduced largely.

It is most suitable for battery drive products such as personal digital

assistant or a cellular phone.

- Quiescent supply current : $I_{CC} = 5 \mu A \text{ (max)} \text{ (Vcc=3.6V)}$
- High-speed operation : tpd=3.0ns (max) ($Vcc=3.3 \pm 0.3V$)

tpd=4.6ns (max) ($Vcc=2.5 \pm 0.2V$) tpd=10.0ns (max) ($Vcc=1.8 \pm 0.15V$)

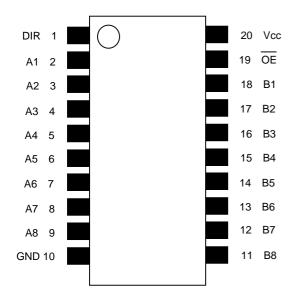
- Output current : I_{OHA}/I_{OLA} (A bus) = $\pm 12mA$ (min) (VCC=3.0V)
 - : I_{OHB}/I_{OLB} (B bus) = $\pm 24mA$ (min) (V_{CC}=3.0V)
- Latch-up performance : ±300mA
- ESD performance : Machine model $> \pm 200V$

: Human body model $> \pm 2000V$

- Ultra-small package : VSSOP (US20)
- Bus hold circuit is built in only the B bus side. (Only in OE=H, a former state is maintained.)
- Floating of A-bus and B-bus are permitted.(When OE=H)
- Gate IC for control(TC7MP01FK) of DIR and OE terminal are prepared.
- 3.6 V tolerant function provided on A-bus terminal, DIR and OE terminal.

Note: At the time bus terminal is enable state, please do not give a signal from the outside.

Pin Assighment (top view)



Truth Table

lı	nput	Bus state	Bus hold circuit
DIR	ŌĒ	bus state	(B bus)
L	L	B A(B=A)	OFF
Н	L	A B(A=B)	OFF
Х	Н	Z	ON*

X: Don't care

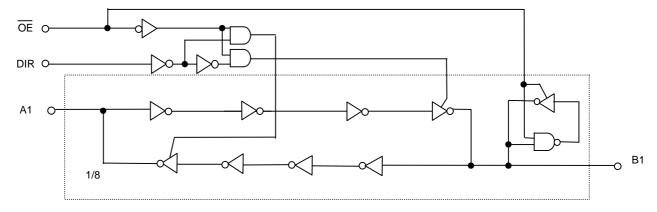
Z: High impedance

Note: When a bus input is in "H" state ,and an output is switched to "enable" to "disable",

Glitch such as "L" state during about 1 to 3ns occurs in an output.

It is not generated when a bus input is in "L" state.

System Diagram



^{*:} Logic state just before becoming disable is maintained.

Maximum Ratings

Parameter	Symbol	Rating	Unit
Power supply voltage	Vcc	- 0.5 to 4.6	V
DC input voltage (DIR, OE)	V _{IN}	- 0.5 to 4.6	V
DC input/output voltage(A bus)	\/I/OA	- 0.5 to 4.6 (Note 1)	V
DC input/output voltage(A bus)	VI/OA	- 0.5 to Vcc+0.5 (Note 2)	V
DC input/output voltage(B bus)	VI/OB	- 0.5 to Vcc+0.5	V
Input diode current(DIR, OE)	I _{IIK}	- 50	mA
Input/Output diode current	I _{I/OK}	± 50	mA
Output current	I _{OUT}	± 50	mA
DC VCC/ground current	I _{CC} /I _{GND}	±100	mA
Power dissipation	P _D	180	mW
Storage temperature	Tstg	- 65 to 150	

Note 1: VCC=0V, or output off state.

Note 2: OE="L", DIR="L"

Recommended Operating Range

Parameter	Symbol	Rating	Unit
Dower oursely veltoge	Vcc	1.65 to 3.6	V
Power supply voltage	VCC	1.2 to 3.6(Note 3)	V
DC input voltage (DIR, OE)	V _{IN}	- 0.3 to 3.6	V
DC input/output voltage(A bus)	VI/OA	0 to 3.6 (Note 4)	V
DC input/output voltage(A bus)	VI/OA	0 to Vcc(Note 5)	V
DC input/output voltage(B bus)	VI/OB	0 to Vcc	V
		± 12 (Note 6)	
Output current (A bus)	I _{OHA} /I _{OLA}	± 9 (Note 7)	mA
		±2(Note 8)	
		±24(Note 6)	
Output current(B bus)	I _{OHB} /I _{OLB}	± 18 (Note 7)	mA
		± 4 (Note 8)	
Operating temperature	Topr	- 40 to 85	
Input rise and fall time	dt/dv	0 to 10 (Note 9)	ns/V

Note 3: Data retention only

Note 4: V_{CC}=0V, or output off state

Note 5: OE="L", DIR="L"

Note 6: V_{CC}=3.0 to 3.6V

Note 7: V_{CC}=2.3 to 2.7V

Note 8: V_{CC}=1.65 to 1.95V

Note 9: V_{IN} =0.8 to 2.0V, V_{CC} =3.0V

Electrical Characteristics

DC Characteristics (Ta=-40 to 85 , 2.7V < Vcc 3.6V)

Paramete	er	Symbol	Те	st Condition	Vcc(V)	Min	Max	Unit	
DC input voltage	H-level	V_{IH}		-	2.7 to 3.6	2.0	-	V	
DC input voltage	L-level	V _{IL}		-	2.7 to 3.6	-	0.8	- V	
				I _{OHA} =-100uA	2.7 to 3.6	Vcc-0.2	-		
	1112		V _{IN} =	I _{OH} =-6mA	2.7	2.2	-		
	H-level	V_{0HA}	V_{IH}	I _{OH} =-9mA	3.0	2.4	-		
Output voltage				I _{OH} =-12mA	3.0	2.2	-	.,	
(A bus)				I _{OLA} =100uA	2.7 to 3.6	-	0.2	- V	
	1.11		V _{IN} =	I _{OL} =6mA	2.7	-	0.4		
	L-level	V_{0LA}	V_{IL}	I _{OL} =9mA	3.0	-	0.4		
				I _{OL} =12mA	3.0	-	0.55		
				I _{OHB} =-100uA	2.7 to 3.6	Vcc-0.2	-		
	H-level	V	V _{IN} =	I _{OHB} =-12mA	2.7	2.2	-		
		V_{OHB}	V_{IH}	I _{OHB} =-18mA	3.0	2.4	-		
Output voltage				I _{OHB} =-24mA	3.0	2.2	-	V	
(B bus)				I _{OLB} =100uA	2.7 to 3.6	-	0.2		
	Libraria	M	V _{IN} =	I _{OLB} =12mA	2.7	-	0.4		
	L-level	V_{0LB}	V_{IL}	I _{OLB} =18mA	3.0	-	0.4		
				I _{OLB} =24mA	3.0	-	0.55		
Input leakage curre	nt(DIR,/OE)	I _{IN}	V	_N =0 to 3.6V	2.7 to 3.6	-	± 5.0	μΑ	
Power off leakag	e current	I _{OFF}	A,DIR	2,/OE=0 to 3.6V	0	-	5.0	μА	
2 state output off o	toto ourrent	I _{OZA}		ut=0 to 3.6V	2.7 to 3.6	-	± 5.0	μА	
3-state output off-s	tate current	I _{OZB}		s=V _{IH} or V _{IL} t=0 or V _{CC}	2.7 to 3.6	-	± 5.0	μА	
Quiescent suppl	y current	I _{cc}	V _{IN} =	=V _{cc} or GND,	2.7 to 3.6	-	5.0	μА	
Increase in ICC per input		I _{CC}		_N =V _{CC} -0.6V per input)	2.7 to 3.6	-	750	μА	
Developed the state	det in the late			V _{IN} =0.8V	0.0	75	-	_	
Bushold input minimum	arive hold current	I _{IHOLD}		V _{IN} =2.0V	3.0	-75	-	- μΑ	
Bushold input over-drive	current to change			(Note 10)	0.5	-	550	μΑ	
state		I_{IOD}		(Note 11)	3.6	-	-550		

Note 10: An external driver must source at least the specified current to switch from LOW-to-HIGH.

Note 11: An external driver must sink at least the specified current to switch from HIGH-to-LOW.

DC Characteristics (Ta=-40 to 85 , 2.3V Vcc 2.7V)

Para	ameter	Symbol	Tes	t Condition	Vcc(V)	Min	Max	Unit	
DC input	H-level	V_{IH}		-	2.3 to 2.7	1.6	-	V	
voltage	L-level	V_{IL}		-		-	0.7	V	
				I _{OHA} =-100uA	2.3 to 2.7	Vcc-0.2	-		
	H-level	V	V _{IN} =	I _{OHA} =-3mA	2.3	2.0	-		
	n-ievei	V_{0HA}	V_{IH}	I _{OHA} =-6mA	2.3	1.8	-		
Output voltage (A bus)				I _{OHA} =-9mA	2.3	1.7	-	V	
(// 505)				I _{OLA} =100uA	2.3 to 2.7	-	0.2		
	L-level	V_{0LA}	V _{IN} = V _{IL}	I _{OLA} =6mA	2.3	-	0.4		
			V IL	I _{OLA} =9mA	2.3	-	0.6		
				I _{OHB} =-100uA	2.3 to 2.7	Vcc-0.2	-		
		V	V _{IN} =	I _{OHB} =-6mA	2.3	2.0	-		
	H-level	V_{0HB}	V_{IH}	I _{OHB} =-12mA	2.3	1.8	-		
Output voltage				I _{OHB} =-18mA	2.3	1.7	-	V	
(B bus)	ous)				I _{OLB} =100uA	2.3 to 2.7	-	0.2	
	L-level	V_{0LB}	V _{IN} = V _{IL}	I _{OLB} =12mA	2.3	-	0.4		
			V IL	I _{OLB} =18mA	2.3	-	0.6	ĺ	
Input leakage	current(DIR,/OE)	I _{IN}	V _{IN}	=0 to 3.6V	2.3 to 2.7	-	± 5.0	μΑ	
Power off le	eakage current	l _{OFF}	A,DIR,	/OE=0 to 3.6V	0	-	5.0	μА	
2 -1-1	-# -t-tt	I _{OZA}	V _{INA} =V _{IH} or V _{IL} Vout=0 to 3.6V		2.3 to 2.7	-	± 5.0	μА	
3-state output	off-state current	I _{OZB}		=V _{IH} or V _{IL} t=0 or V _{CC}	2.3 to 2.7	-	± 5.0	μА	
Quiescent s	supply current	I _{cc}	V _{IN} =V _{CC} or GND,		2.3 to 2.7	-	5.0	μА	
Bushold input m	ninimum drive hold		,	V _{IN} =0.7V	0.0	45	-		
	rrent	I _{IHOLD}	V _{IN} =1.6V		2.3	-45	-	μА	
Bushold input or	ver-drive current to		(Note 12)	0.7	-	400	μΑ	
	ge state	I _{IOD}	(Note 13)	2.7	-	-400		

Note 12: An external driver must source at least the specified current to switch from LOW-to-HIGH.

Note 13: An external driver must sink at least the specified current to switch from HIGH-to-LOW.

DC Characteristics (Ta=-40 to 85 , 1.65V Vcc < 2.3V)

Para	ımeter	Symbol	Tes	t Condition	Vcc(V)	Min	Max	Unit	
DC input	H-level	V_{IH}		-	1.65 to 2.3	0.7 × V c c	-	V	
voltage	L-level	V _{IL}		-	1.65 to 2.3	-	0.2 × Vcc	V	
	H-level	V	V _{IN} =	I _{OHA} =-100uA	1.65	Vcc-0.2	-		
Output voltage	n-ievei	V_{0HA}	V _{IH}	I _{OHA} =-2mA	1.65	1.3	-		
(A bus)	L-level	V_{0LA}	V _{IN} =	I _{OLA} =2mA	1.65	-	0.2	V	
		.,	V _{IN} =	I _{OHB} =-100uA	1.65	Vcc-0.2	-		
Output voltage	H-level	V_{0HB}	V _{IH}	I _{OHB} =-4mA	1.65	1.3	-		
(B bus)	L-level	V_{0LB}	V _{IN} = V _{IL}	I _{OLB} =4mA	1.65	-	0.2	V	
Input leakage of	current(DIR,/OE)	I _{IN}	V _{IN} =0 to 3.6V		1.65 to 2.3	-	± 5.0	μА	
Power off lea	akage current	I _{OFF}	A,DIR,/OE=0 to 3.6V		0	-	5.0	μА	
2 state output	off atota aureant	I _{OZA}		=V _{IH} or V _{IL} t=0 to 3.6V	1.65 to 2.3	-	± 5.0	μА	
3-state output	3-state output off-state current			=V _{IH} or V _{IL} t=0 or V _{CC}	1.65 to 2.3	-	± 5.0	μА	
Quiescent s	supply current	I _{cc}	V _{IN} =V _{CC} or GND,		1.65 to 2.3	-	5.0	μА	
Bushold input minimum drive hold		I _{I(HOLD)}	٧	′ _{IN} =0.33V	1.65	20	-	^	
	current		V	′ _{IN} =1.16V	1.65	-20	-	μА	
	over-drive current	1	(Note 14)	1.95	-	300		
to char	nge state	I _{I(OD)}	((Note 15)		-	-300	μА	

Note 14: An external driver must source at least the specified current to switch from LOW-to-HIGH.

Note 15: An external driver must sink at least the specified current to switch from HIGH-to-LOW.



AC Characteristics (Ta=-40 to 85 ,Input: tr=tf=2.0ns,CL=30pF ,RL=500)

Parameter	Symbol	Test Condition	Vcc(V)	Min	Max	Unit
			1.8 ± 0.15	1.0	10.0	
Propagation delay time	tpLH tpHL	Figure 1, Figure 2	2.5 ± 0.2	0.8	4.6	ns
	4		3.3 ± 0.3	0.6	3.0	
			1.8 ± 0.15	1.0	15.0	
3-state output enable time	tpZL tpZH	Figure 1, Figure 3	2.5 ± 0.2	0.8	7.8	ns
	4		3.3 ± 0.3	0.6	5.6	
			1.8 ± 0.15	1.0	6.5	
3-state output disable time	tpLZ tpHZ	Figure 1, Figure 3	2.5 ± 0.2	0.8	4.3	ns
	φπΖ		3.3 ± 0.3	0.6	3.9	
			1.8 ± 0.15	-	0.5	
Output to output skew	tosLH tosHL	(Note 16)	2.5 ± 0.2	-	0.5	ns
			3.3 ± 0.3	-	0.5	

For C_L=50pF, add approximately 300ps to the AC maximum specification.

Note 16: Parameter guaranteed by design.

 $(tosLH = |t_{pLHm} - t_{pLHn}|, tosHL = |t_{pHLm} - t_{pHLn}|)$

Capacitive Characteristics(Ta=25)

Characteristics	Symbol	Test Condition	Vcc(V)	Тур.	Unit
Input capacitance	C _{IN}		1.8,2.5,3.3	6	pF
Bus I/O capacitance	C I/O		1.8,2.5,3.3	7	pF
Power dissipation	CPDA	OE="L",finA=100MH z Table 1 (Note 17)	1.8,2.5,3.3	20	pF
capacitance	CIDA	OE=" H ",finA=100MH z Table 1 (Note 17)	1.0,2.0,0.0	0	pF
Power dissipation	CPDB	OE="L",finB=100MH z Table 1 (Note 17)	1.8,2.5,3.3	16	pF
capacitance	OI DB	OE=" H ",finB=100MH z Table 1 (Note 17)	1.0,2.0,0.0	1	pF

Note17: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation.

I_{CC(opr)} =C_{PD}·V_{CC}·V_{IN}+I_{CC}/8(per bit)

Table1	CPD	Test	Condition
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Function										Р	in									
Function	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20
A bus /OE= "L"	Н	Р	Χ	Χ	Χ	Χ	Χ	Χ	Χ	G	0	0	0	0	0	0	0	С	L	V
A bus /OE= "H"	Н	Р	0	0	0	0	0	0	0	G	0	0	0	0	0	0	0	0	Н	V
B bus /OE= "L"	L	С	0	0	0	0	0	0	0	G	Х	Х	Х	Х	Х	Х	Х	Р	L	V
B bus /OE= "H"	L	0	0	0	0	0	0	0	0	G	0	0	0	0	0	0	0	Р	Н	V

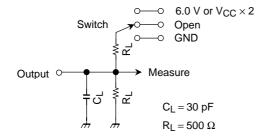
- Symbol explanation -

V=V_{CC}(+3.3V) X=Don't care(Fixed to V_{CC} or GND)

G=GND(0V) O=Open

L=Logic0(GND) P=Input pulse with 50% duty cycle.

AC Test Circuit



Parameter	Switch			
t _{pLH} , t _{pHL}		Open		
^t pLZ ^{, †} pZL	6.0 V V _{CC} × 2	$@V_{CC} = 3.3 \pm 0.3 \text{ V}$ $@V_{CC} = 2.5 \pm 0.2 \text{ V}$ $@V_{CC} = 1.8 \pm 0.15 \text{ V}$		
t _{pHZ} , t _{pZH}	GND			

Figure 1

AC Waveform

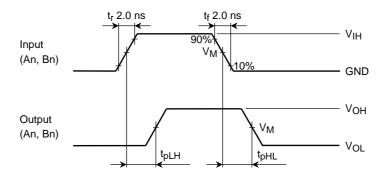


Figure 2 tpLH, tpHL

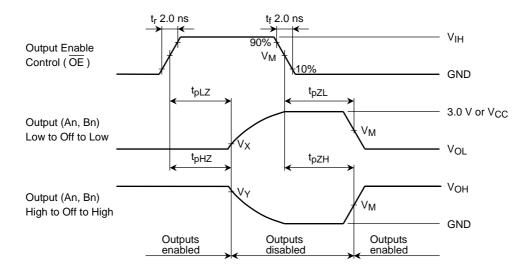
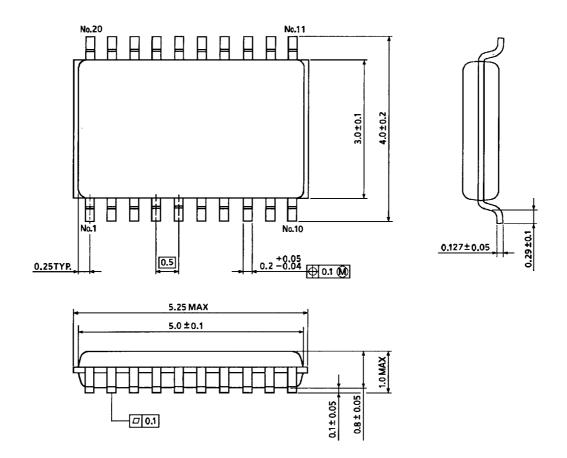


Figure 3 $t_{pLZ}, t_{pHZ}, t_{pZL}, t_{pZH}$

Symbol	Vcc							
Symbol	$3.3 \pm 0.3 \text{ V}$	2.5 ± 0.2 V	1.8 ± 0.15 V					
V _{IH}	2.7 V	V _{CC}	V _{CC}					
V_{M}	1.5 V	V _{CC} /2	V _{CC} /2					
VX	V _{OL} + 0.3 V	V _{OL} + 0.15 V	V _{OL} + 0.15 V					
VY	V _{OH} - 0.3 V	V _{OH} - 0.15 V	V _{OH} - 0.15 V					

Package Dimensions



Weight: 0.03 g (typ.)

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000707EBA

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